

Title (en)
METHOD FOR DOPING SILICON SHEETS

Title (de)
VERFAHREN ZUR DOTIERUNG VON SILICIUMFOLIEN

Title (fr)
PROCEDE DE DOPAGE DE PLAQUES DE SILICIUM

Publication
EP 2976782 A1 20160127 (FR)

Application
EP 14711268 A 20140320

Priority
• FR 1300650 A 20130320
• EP 2014055621 W 20140320

Abstract (en)
[origin: WO2014147185A1] The invention relates to a method for doping a silicon sheet for producing a photovoltaic cell, said method comprising the steps consisting of: carrying out a first doping of at least one first part (11) of a surface (10) of the silicon sheet; forming an oxide layer (40) on the partially doped surface (10); and carrying out a second doping via the oxide layer (40), such that another part (12) of the surface (10) of the silicon sheet is doped.

IPC 8 full level
H01L 21/223 (2006.01); **H01L 29/10** (2006.01); **H01L 31/18** (2006.01)

CPC (source: EP US)
H01L 21/2236 (2013.01 - EP US); **H01L 31/068** (2013.01 - EP US); **H01L 31/1804** (2013.01 - EP US); **H01L 31/186** (2013.01 - US); **Y02E 10/547** (2013.01 - EP US); **Y02P 70/50** (2015.11 - EP US)

Citation (search report)
See references of WO 2014147185A1

Citation (examination)
JP S59155164 A 19840904 - TOSHIBA KK

Designated contracting state (EPC)
AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

Designated extension state (EPC)
BA ME

DOCDB simple family (publication)
WO 2014147185 A1 20140925; CN 105580110 A 20160511; EP 2976782 A1 20160127; FR 3003687 A1 20140926; FR 3003687 B1 20150717; JP 2016520996 A 20160714; KR 20150133739 A 20151130; US 2016204299 A1 20160714; US 2019164761 A1 20190530

DOCDB simple family (application)
EP 2014055621 W 20140320; CN 201480017013 A 20140320; EP 14711268 A 20140320; FR 1300650 A 20130320; JP 2016503664 A 20140320; KR 20157027263 A 20140320; US 201414777798 A 20140320; US 201916249130 A 20190116